



# High Efficiency Thyristor

$V_{RRM} = 1200\text{ V}$

$I_{TAV} = 30\text{ A}$

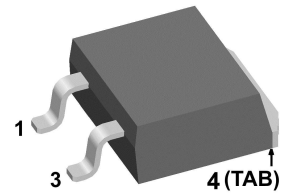
$V_T = 1.27\text{ V}$

## Single Anode Gated Thyristor

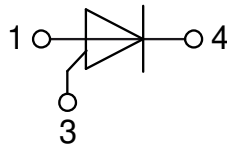
**Part number**

**CLB30I1200PZ**

Marking on Product: CLB30I1200PZ



Backside: cathode



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Thyristor can be used as Triac
  - anti-parallel combination with CGT
  - Cathode-Gated-Thyristor covers quadrants I & II
  - CGT-counterpart: CLA30E1200NPZ

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

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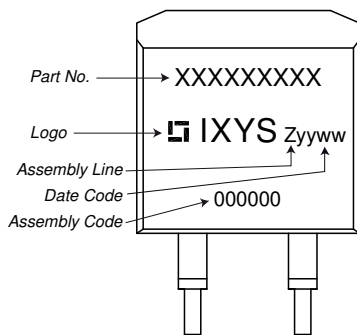


Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		10	$\mu A$
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$		2	mA
$V_T$	forward voltage drop	$I_T = 30 A$	$T_{VJ} = 25^{\circ}C$		1.30	V
		$I_T = 60 A$			1.59	V
		$I_T = 30 A$	$T_{VJ} = 125^{\circ}C$		1.27	V
		$I_T = 60 A$			1.65	V
$I_{TAV}$	average forward current	$T_C = 115^{\circ}C$	$T_{VJ} = 150^{\circ}C$		30	A
$I_{T(RMS)}$	RMS forward current	180° sine			47	A
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.86	V
$r_T$	slope resistance				13.2	m $\Omega$
$R_{thJC}$	thermal resistance junction to case				0.5	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		250	W
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		300	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		325	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		255	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		275	A
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		450	A <sup>2</sup> s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		440	A <sup>2</sup> s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		325	A <sup>2</sup> s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		315	A <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		13	pF
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		10	W
		$t_p = 300 \mu s$			5	W
$P_{GAV}$	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 \text{ Hz}$	repetitive, $I_T = 90 A$		150	A/ $\mu s$
		$t_p = 200 \mu s; di_G/dt = 0.3 A/\mu s;$ $I_G = 0.3 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 30 A$		500	A/ $\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		500	V/ $\mu s$
		$R_{GK} = \infty$ ; method 1 (linear voltage rise)				
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.3	V
			$T_{VJ} = -40^{\circ}C$		1.6	V
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		30	mA
			$T_{VJ} = -40^{\circ}C$		50	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0.2	V
$I_{GD}$	gate non-trigger current				1	mA
$I_L$	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		90	mA
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$				
$I_H$	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		60	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	$\mu s$
		$I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$				
$t_q$	turn-off time	$V_R = 100 V; I_T = 30 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	$\mu s$



Package TO-263 (D2Pak-HV)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			35	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				1.5		g
$F_C$	mounting force with clip		20		60	N
$d_{Spp/ App}$	creepage distance on surface / striking distance through air	terminal to terminal	4.2			mm
$d_{Spb/ Apb}$		terminal to backside	4.7			mm

**Product Marking**



**Part description**

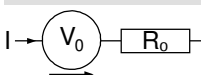
- C = Thyristor (SCR)
- L = High Efficiency Thyristor
- B = Anode gated (up to 1200V)
- 30 = Current Rating [A]
- I = Single Anode Gated Thyristor
- 1200 = Reverse Voltage [V]
- PZ = TO-263AB (D2Pak) (2HV)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLB30I1200PZ-TRL	CLB30I1200PZ	Tape & Reel	800	516337
Alternative	CLB30I1200PZ-TUB	CLB30I1200PZ	Tube	50	525283

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150\text{ °C}$

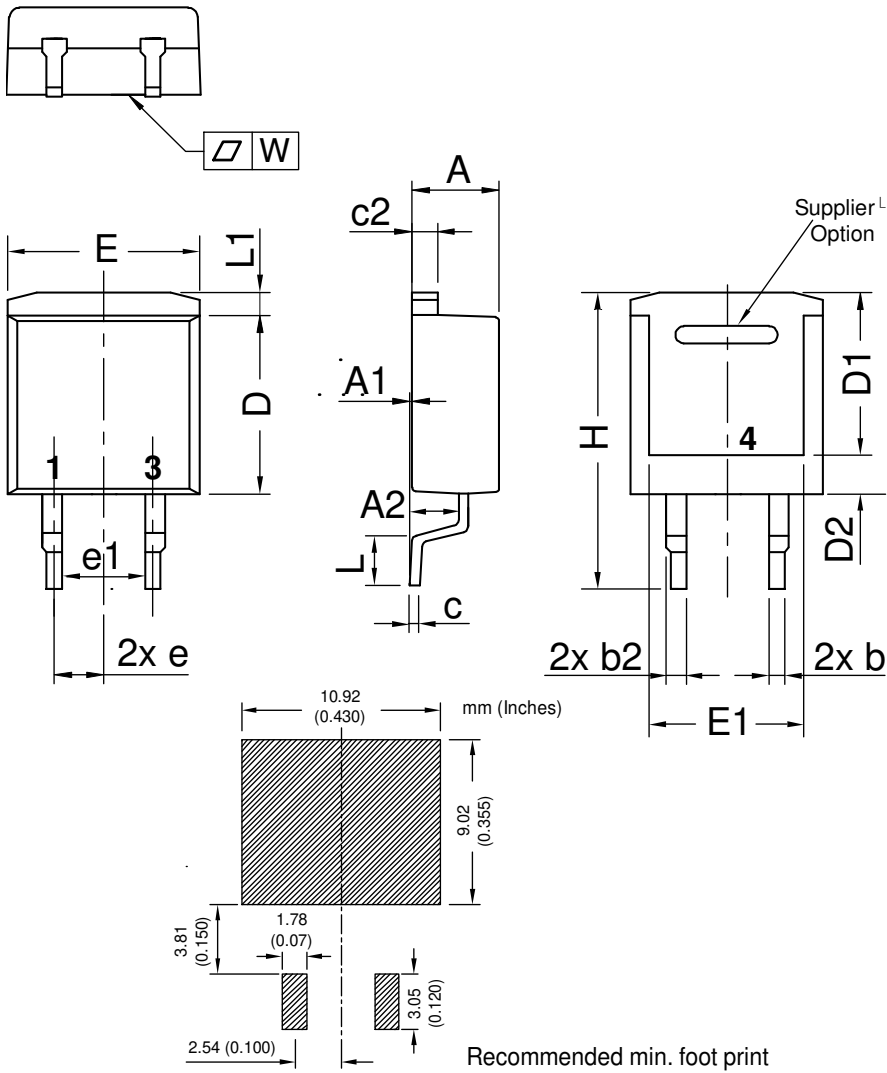


**Thyristor**

$V_{0\ max}$	threshold voltage	0.86	V
$R_{0\ max}$	slope resistance *	10	mΩ

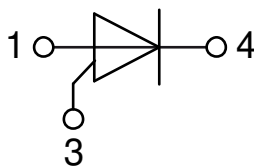


**Outlines TO-263 (D2Pak-HV)**



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.3		0.091	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

*All dimensions conform with and/or within JEDEC standard.*



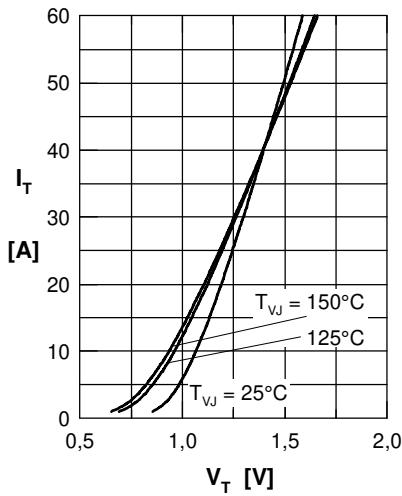
**Thyristor**


Fig. 1 Forward characteristics

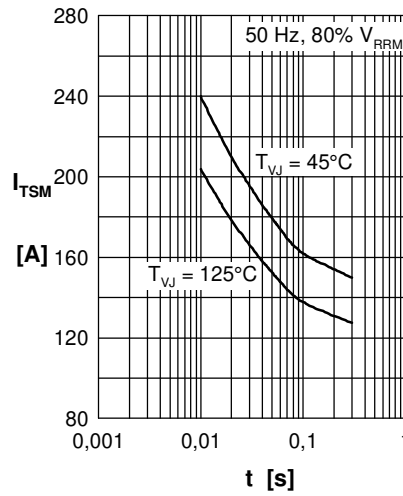
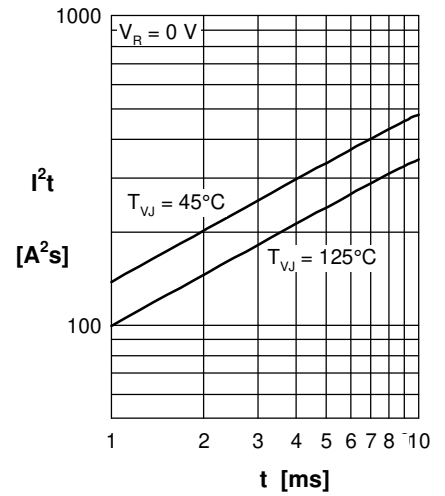
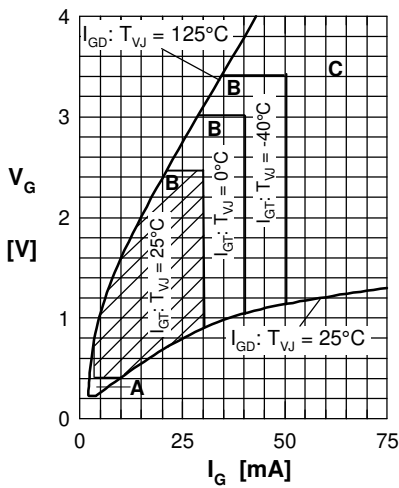
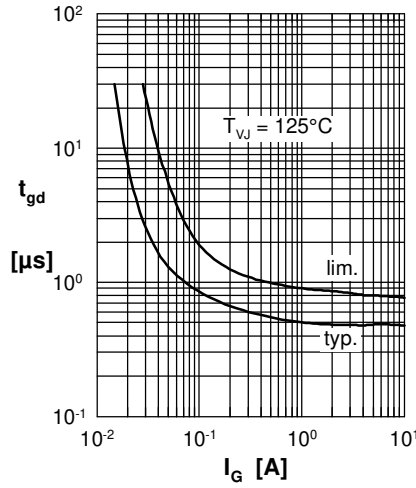
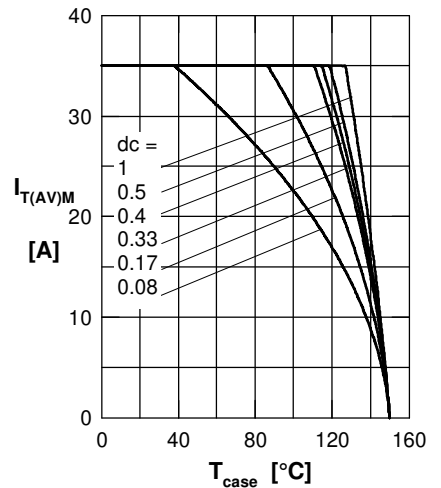

 Fig. 2 Surge overload current  
 $I_{TSM}$ : crest value,  $t$ : duration

 Fig. 3  $I^2t$  versus time (1-10 s)

 Fig. 4 Gate voltage & gate current  
 Triggering: A = no; B = possible; C = safe

 Fig. 5 Gate controlled delay time  $t_{gd}$ 


Fig. 6 Max. forward current at case temperature

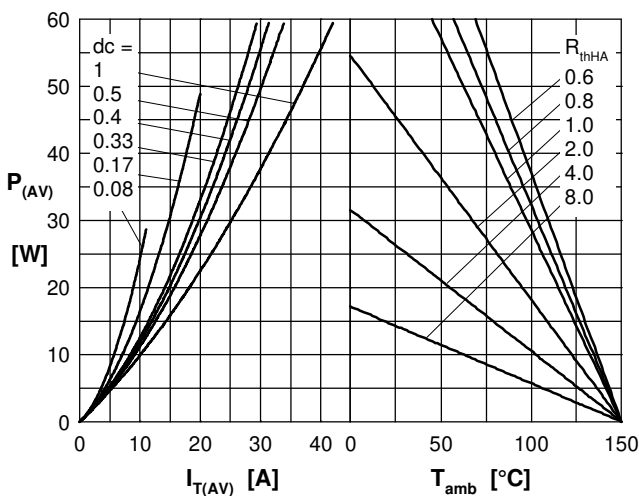
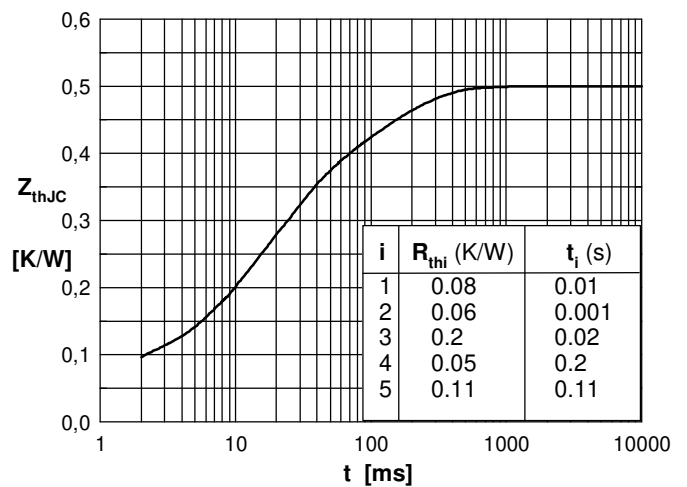

 Fig. 7a Power dissipation versus direct output current  
 Fig. 7b and ambient temperature


Fig. 7 Transient thermal impedance junction to case

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